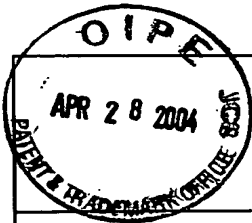


04-30-04



**U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE**

**INFORMATION DISCLOSURE
STATEMENT**

Docket Number:
10746/33A

Application Number
10/775,806

Filing Date
February 9, 2004

Examiner
Not Yet Assigned

Art Unit
Not Yet Assigned

Title
SEMICONDUCTOR OPTICAL DEVICE AND
THE FABRICATION METHOD

Applicant(s)
Susumu KONDO et al.

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

1. In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 35 U.S.C. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorneys for Applicants hereby bring the following references to the attention of the Examiner. These references are listed on the attached modified PTO Form No. 1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom. The filing of this Information Disclosure Statement and the enclosed PTO Form No. 1449, shall not be construed as an admission that the information cited is prior art, or is considered to be material to patentability as defined in 37 C.F.R. § 1.56(b).
2. Copies are enclosed of each patent, publication or other information listed on the modified PTO Form 1449 marked with an asterisk. Otherwise, copies of each patent, publication or other information listed on the modified PTO Form 1449 are not enclosed since they were previously cited by or submitted to the Patent Office in a prior application, Serial No. 10/124,835, which is relied upon for an earlier filing date under 35 U.S.C. 120.
3. It is believed that no fees are due in connection with this Information Disclosure Statement. However, should any fees be due, the Commissioner is authorized to charge Deposit Account No. 11-0600 for such fees. A duplicate copy of this communication is enclosed for charging purposes.

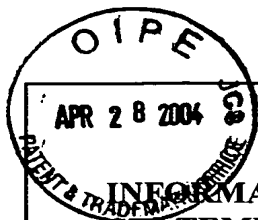
Dated: _____

By: _____

Aaron C. Deditch (Reg. No. 33,865)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. 10746/33A	U.S. SERIAL NO. 10/775,806
	APPLICANT(S) Susumu KONDO et al.	
	FILING DATE February 9, 2004	GROUP Not Yet Assigned

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Page 1 of 2

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	9-214045	August 15, 1997	Japan			X	
	61-290790	December 20, 1986	Japan			X	
	8-250806	September 27, 1996	Japan			X	
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		Y. Toyoda, K. Wakita, "Phase Evaluation of Tensile Strained Quantum Well Modulators", Extended Abstracts (The 62 nd Autumn Meeting, 2001); The Japan Society of Applied Physics, September 2001, 1 page and English translation.
		S. Kondo, Y. Noguchi, K. Tsuzuki, M. Yuda, S. Oku, Y. Kondo, "Ru-doped Semi-Insulating InP buried InGaAlAs/InAlAs MQWs modulators", Extended Abstracts (The 62 nd Autumn Meeting, 2001); The Japan Society of Applied Physics, September 2001, 1 page and English translation.
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		S. Kondo, Y. Noguchi, K. Tsuzuki, M. Yuda, S. Oku, Y. Kondo, H. Takeuchi, "Ruthenium-doped semi-insulating InP buried InGaAlAs/InAlAs MQWs modulators, 13 th IPRM May 2001, pp. 19-20.

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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U. S. PATENT DOCUMENTS

Page 2 of 2

EXAMINER INITIAL	PATENT NUMBER	PATENT DATE	NAME	CLASS	SUBCLASS	FILING DATE*

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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		D. Soderstrom et al., "Electrical Characterization of Ruthenium-Doped InP Grown by Low Pressure Hydride Vapor Phase Epitaxy", Electrochemical and Solid-state Letters, 4(6) G53-G55 (2001).
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